Dependence of the electronic structure of self-assembled $(\mathrm{In},\mathrm{Ga})\mathrm{As}/\mathrm{GaAs}$ quantum dots on height and composition

Gustavo A. Narvaez, Gabriel Bester, and Alex Zunger

Citation: Journal of Applied Physics 98, 043708 (2005); doi: 10.1063/1.1980534

Dependence of the electronic structure of self-assembled (In,Ga)As/GaAs quantum dots on height and composition

G a A. Na a , Ga B , a A x Z a)
, , 80401

[illegible]

R

IV. SUMMARY

2. Number of k points

[illegible] $\mathbf{k}$ [illegible] $\mathbf{k}$ [illegible]
Γ

[illegible] **76** [illegible] ([illegible])-

[illegible] **224** [illegible] ([illegible])-